Please amend the claims as follows:

Claim 1 (currently amended): An epoxy resin composition for semiconductor sealing encapsulating comprising an epoxy resin, a phenol resin, an inorganic filler, a curing accelerator, and a carbon precursor having a specific electric resistivity in a semiconductor region of $1 \times 10^2 \, \underline{\Omega}$ cm or more but less than $1 \times 10^7 \, \underline{\Omega}$ cm as essential components, wherein the amounts of the inorganic filler and the carbon precursor in the epoxy resin composition are respectively 65-92 wt% and 0.1-5.0 wt%.

Claim 2 (currently amended): The epoxy resin composition for semiconductor sealing encapsulating according to claim 1, wherein the carbon precursor has an H/C ratio by weight determined by elemental analysis of 2/97 to 4/93.

Claim 3 (currently amended): The epoxy resin composition for semiconductor sealing encapsulating according to claim 1, wherein the carbon precursor is fine particles having an average particle diameter of 0.5-50 µm.

Claim 4 (currently amended): The epoxy resin composition for semiconductor sealing encapsulating according to claim 1, wherein the carbon precursor is fine particles having an average particle diameter of 0.5-20 µm.

Claim 5 (currently amended): The epoxy resin composition for semiconductor sealing encapsulating according to claim 1, wherein the carbon precursor has a specific electric resistivity of $1 \times 10^4 \, \underline{\Omega}$ cm or more but less than $1 \times 10^7 \, \underline{\Omega}$ cm.

Claim 6 (currently amended): The epoxy resin composition for semiconductor sealing-encapsulating according to claim 1, wherein the amount of the inorganic filler in the total amount of the epoxy resin composition is 70-91 wt%.

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Application No. 10/821,852 Inventor: Masakatsu MAEDA

Preliminary Amendment

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Claim 7 (currently amended): The epoxy resin composition for semiconductor sealing-encapsulating according to claim 1, wherein the carbon precursor is produced by carbonizing a phenol resin at a calcination temperature of 600-650°C.

Claim 8 (currently amended): A semiconductor device comprising a semiconductor element sealed-encapsulated using the epoxy resin composition for semiconductor sealing encapsulating according to any one of claims 1-7.